

2SK1808

Silicon N Channel MOS FET

REJ03G0975-0200
(Previous: ADE-208-1322)
Rev.2.00
Sep 07, 2005

Application

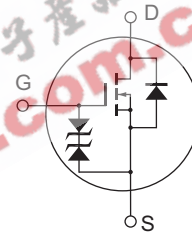
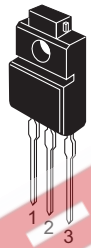
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator, DC-DC converter

Outline

RENESAS Package code: PRSS0003AD-A
(Package name: TO-220FM)



1. Gate
2. Drain
3. Source

Absolute Maximum Ratings

(Ta = 25°C)

| Item | Symbol | Ratings | Unit |
|---|---------------------|-------------|------|
| Drain to source voltage | V_{DSS} | 900 | V |
| Gate to source voltage | V_{GSS} | ±30 | V |
| Drain current | I_D | 4 | A |
| Drain peak current | $I_{D(pulse)}^{*1}$ | 10 | A |
| Body to drain diode reverse drain current | I_{DR} | 4 | A |
| Channel dissipation | P_{ch}^{*2} | 35 | W |
| Channel temperature | T_{ch} | 150 | °C |
| Storage temperature | T_{stg} | -55 to +150 | °C |

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1 \%$
 2. Value at $T_c = 25^\circ C$

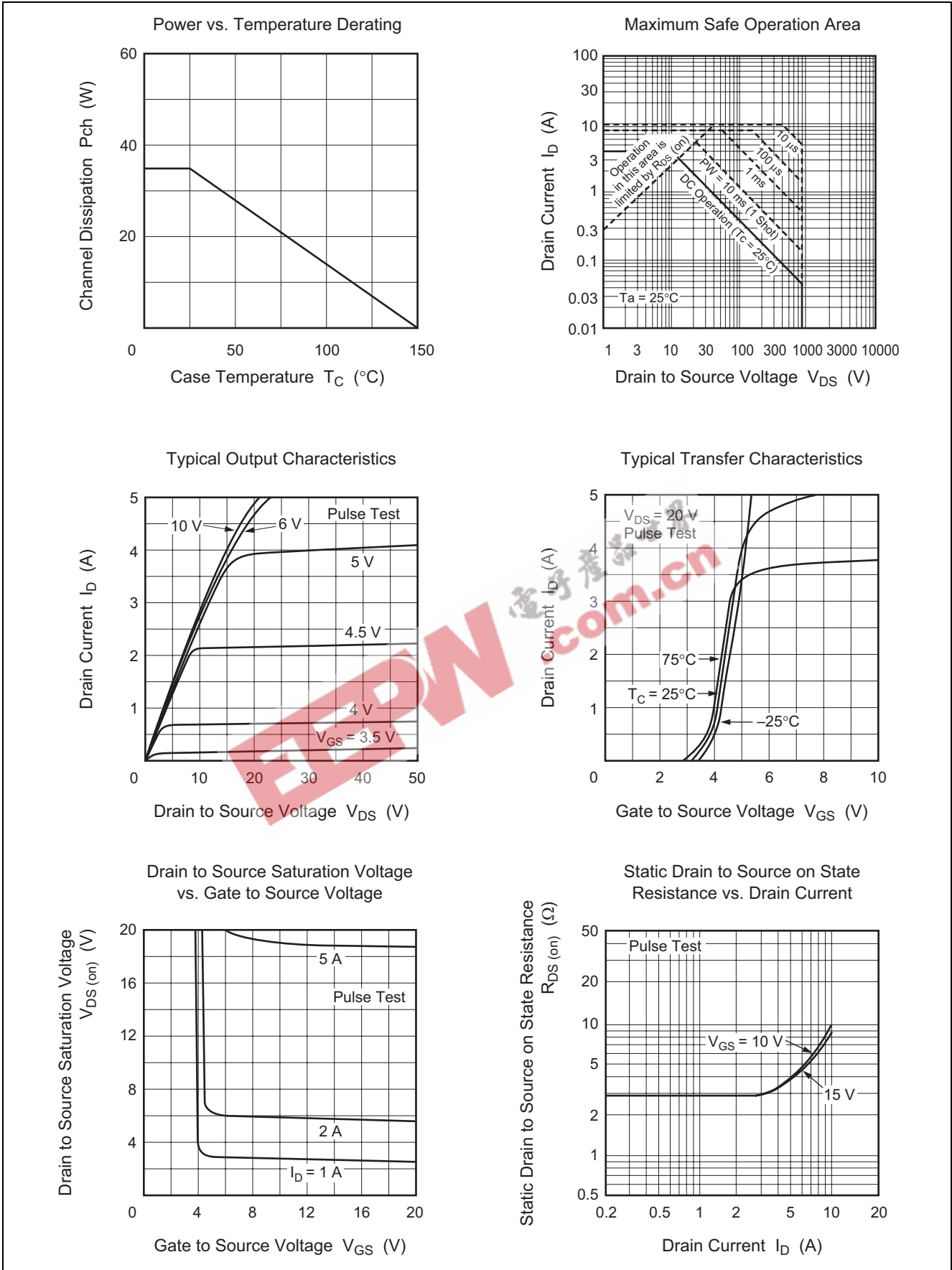
Electrical Characteristics

(Ta = 25°C)

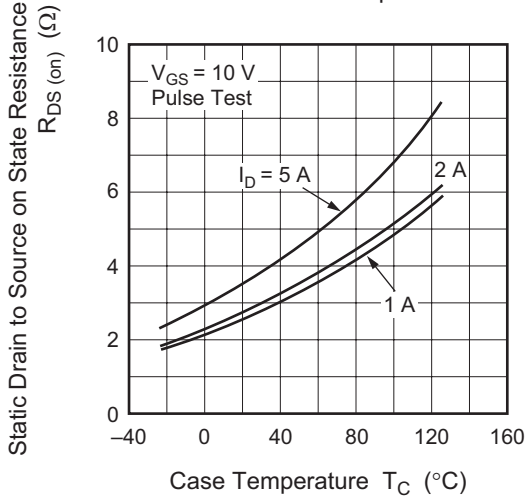
| Item | Symbol | Min | Typ | Max | Unit | Test Conditions |
|--|---------------|-----|-----|-----|------|---|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | 900 | — | — | V | $I_D = 10 \text{ mA}$, $V_{GS} = 0$ |
| Gate to source breakdown voltage | $V_{(BR)GSS}$ | ±30 | — | — | V | $I_G = \pm 100 \mu A$, $V_{DS} = 0$ |
| Gate to source leak current | I_{GSS} | — | — | ±10 | μA | $V_{GS} = \pm 25 \text{ V}$, $V_{DS} = 0$ |
| Zero gate voltage drain current | I_{DSS} | — | — | 250 | μA | $V_{DS} = 720 \text{ V}$, $V_{GS} = 0$ |
| Gate to source cutoff voltage | $V_{GS(off)}$ | 2.0 | — | 3.0 | V | $I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$ |
| Static drain to source on state resistance | $R_{DS(on)}$ | — | 3.0 | 4.0 | Ω | $I_D = 2 \text{ A}$, $V_{GS} = 10 \text{ V}^{*3}$ |
| Forward transfer admittance | $ y_{fs} $ | 1.7 | 2.7 | — | S | $I_D = 2 \text{ A}$, $V_{DS} = 20 \text{ V}^{*3}$ |
| Input capacitance | C_{iss} | — | 740 | — | pF | $V_{DS} = 10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$ |
| Output capacitance | C_{oss} | — | 305 | — | pF | |
| Reverse transfer capacitance | C_{rss} | — | 150 | — | pF | |
| Turn-on delay time | $t_{d(on)}$ | — | 15 | — | ns | $I_D = 2 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_L = 15 \Omega$ |
| Rise time | t_r | — | 60 | — | ns | |
| Turn-off delay time | $t_{d(off)}$ | — | 100 | — | ns | |
| Fall time | t_f | — | 80 | — | ns | |
| Body to drain diode forward voltage | V_{DF} | — | 0.9 | — | V | $I_F = 4 \text{ A}$, $V_{GS} = 0$ |
| Body to drain diode reverse recovery time | t_{rr} | — | 800 | — | ns | $I_F = 4 \text{ A}$, $V_{GS} = 0$, $di_F/dt = 100 \text{ A}/\mu s$ |

Note: 1. Pulse Test

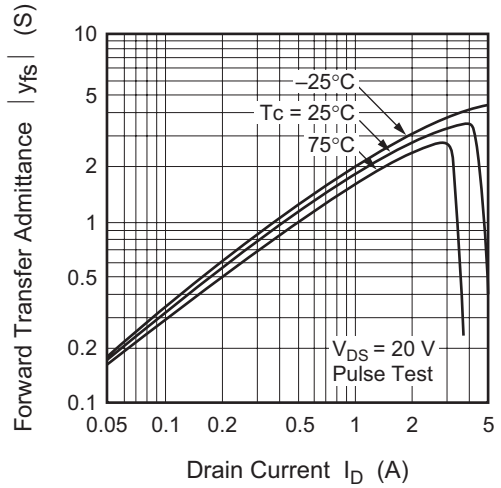
Main Characteristics



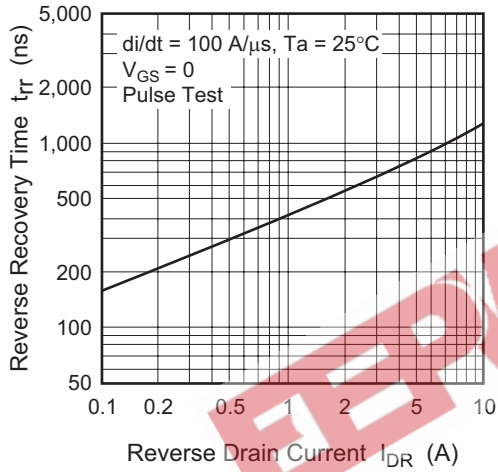
Static Drain to Source on State Resistance vs. Temperature



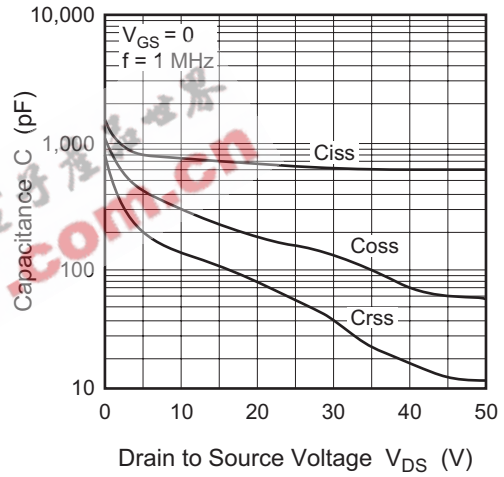
Forward Transfer Admittance vs. Drain Current



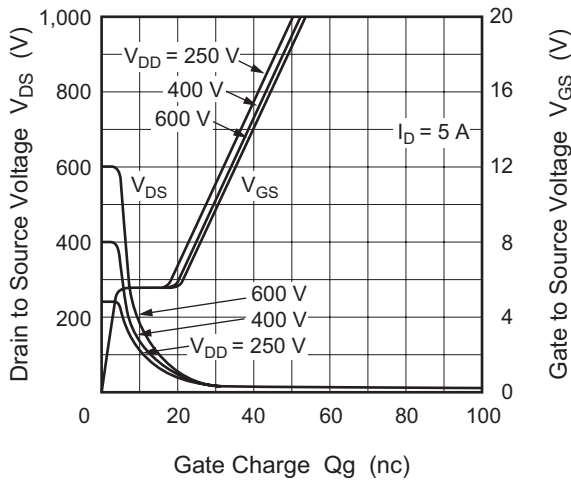
Body to Drain Diode Reverse Recovery Time



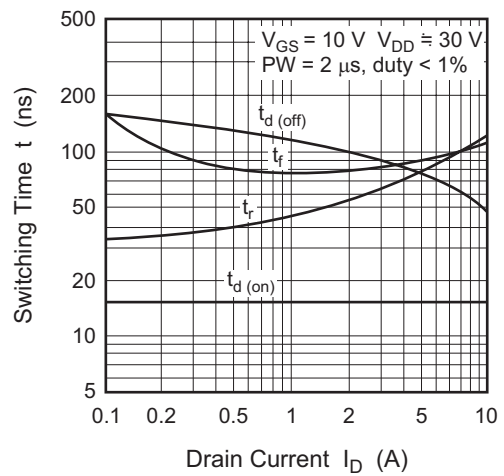
Typical Capacitance vs. Drain to Source Voltage



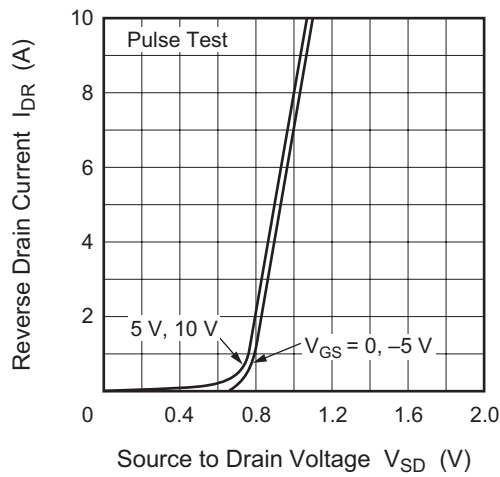
Dynamic Input Characteristics



Switching Characteristics

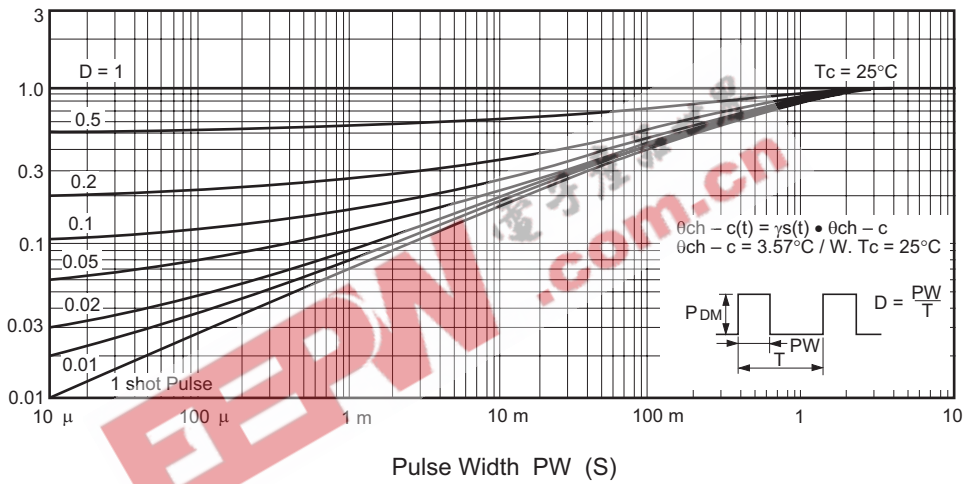


Reverse Drain Current vs. Source to Drain Voltage

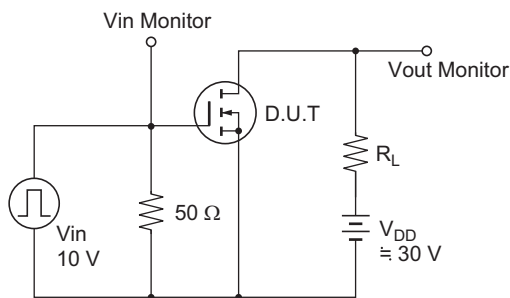


Normalized Transient Thermal Impedance $\gamma_s(t)$

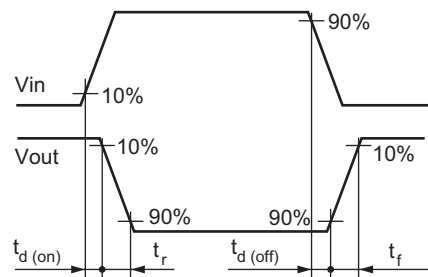
Normalized Transient Thermal Impedance vs. Pulse Width



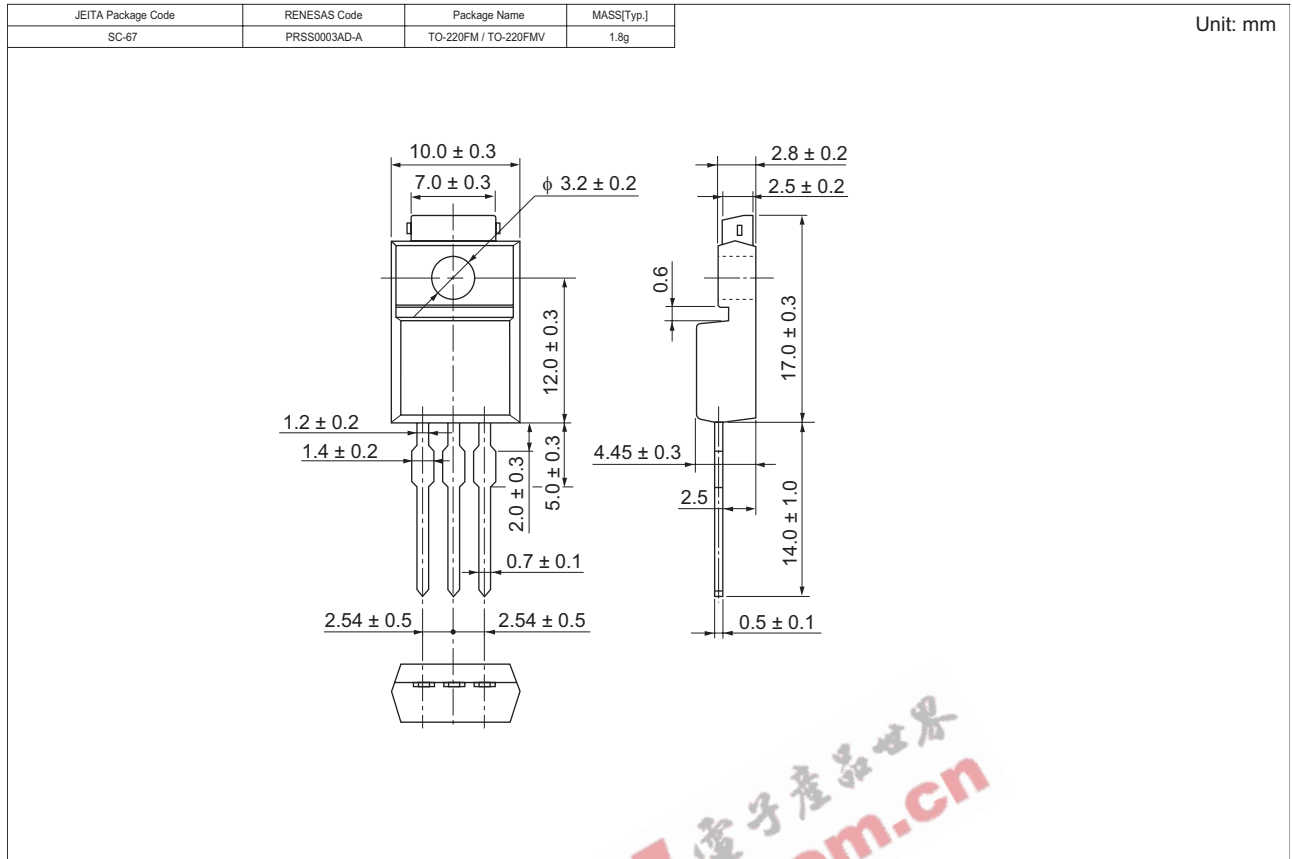
Switching Time Test Circuit



Waveforms



Package Dimensions



Ordering Information

| Part Name | Quantity | Shipping Container |
|-----------|----------|--------------------|
| 2SK1808-E | 500 pcs | Box (Sack) |

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510